

**Amendments to the Claims:**

This listing of claims replaces all prior versions, and listings, of claims of this application:

**In the Claims:**

Claims 1-3 (Canceled).

4. (Previously presented) A method according to Claim 16 further comprising:  
forming the gap in the substrate through a hard mask thereon prior to forming the first material in the gap.

5. (Previously presented) A method according to Claim 4 further comprising:  
removing the hard mask from the substrate prior to selectively depositing the top oxide layer in the gap.

6. (Previously presented) A method according to Claim 16 wherein a first rate in a first direction toward an opening is about four times greater than a second rate in a second direction away from the side walls of the gap.

7. (Previously presented) A method according to Claim 16 wherein a depth of the gap is at least about eight times greater than a width of the gap.

8. (Previously presented) A method according to Claim 16 wherein the first material comprises a first oxide layer and wherein depositing an oxide material comprises:  
introducing an ozone amount in a range between about 1 liter and about 18 liters to provide a concentration in a range between about 1.0% by weight and about 18% by weight to an environment containing the substrate; and  
introducing a TEOS to the environment at a rate in a range between about \_sccm and about 1200 sccm.

9. (Currently Amended) A method of forming material in a gap in a substrate, the method comprising:

forming a pattern to define a gap on a substrate, wherein an upper surface of the pattern and sidewalls of the gap comprise a non-oxide layer;

forming a bottom oxide layer on a surface of the substrate and substantially filling the gap;

etching back the bottom oxide layer inside an opening in the gap to expose the upper surface of the pattern and side walls of the gap so that a residual bottom oxide layer remains only at a bottom of the gap; and

selectively growing a top oxide layer on the residual bottom oxide layer faster than on the non-oxide layer.

10. (Original) A method according to Claim 9 wherein forming a pattern comprises:

forming a hard mask pattern exposing a part of the substrate;  
etching the substrate using the hard mask pattern as an etch mask to form the gap; and  
conformally depositing a silicon nitride layer liner on a surface of the substrate including on the side walls of the gap.

11. (Original) A method Claim 9 wherein the step of forming a pattern comprises:  
forming a hard mask pattern on the substrate exposing a part of the substrate;  
etching the substrate using the hard mask pattern as the etch mask to form the trench;  
and  
removing the hard mask pattern.

12. (Original) A method according to Claim 11 wherein forming a trench oxide layer inner sidewall in the trench is performed before removing the hard mask pattern.

13. (Original) A method according to Claim 9 wherein the top oxide layer is formed using ozone and TEOS as a source gas at a pressure in a range between about 200 torr

and about 760 torr and at a temperature in a range between about 400°C to 480°C temperature in an environment containing the substrate.

14. (Original) A method according to Claim 13 wherein an amount of ozone in a range between about 1 liter to about 18 liters is introduced to provide a concentration is a range between about 1% by weight and about 18% by weight, and TEOS is provided a rate in a range between about 100sccm and about 1200sccm.

15. (Original) A method according to Claim 9 wherein forming a bottom oxide layer comprises forming the bottom oxide layer to a thickness in a range between about 100 Angstroms and about 3600 Angstroms.

16. (Currently Amended) A method of forming material in a gap in a substrate, the method comprising:

forming a bottom oxide layer only at a bottom of a gap in the substrate; and

selectively growing a top oxide layer on the bottom oxide layer wherein the top oxide layer is formed on the bottom oxide layer at a faster rate than on non-oxide materials.